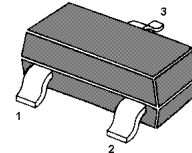


# PNP Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into three groups O, Y and G, according to its DC current gain. As complementary type the NPN transistor MMBTSC1815 is recommended.



1.Base 2.Emitter 3.Collector  
SOT-23 Plastic Package

## Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	50	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	150	mA
Base Current	$-I_B$	50	mA
Power Dissipation	$P_{tot}$	200	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_S$	- 65 to +150	$^\circ\text{C}$

## Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit	
DC Current Gain at $-V_{CE} = 6\text{ V}$ , $-I_C = 2\text{ mA}$  at $-V_{CE} = 6\text{ V}$ , $-I_C = 150\text{ mA}$  Current Gain Group	O	$h_{FE}$	70	140	-
	Y	$h_{FE}$	120	240	-
	G	$h_{FE}$	200	400	-
		$h_{FE}$	25	-	-
Collector Base Cutoff Current at $-V_{CB} = 50\text{ V}$	$-I_{CBO}$	-	0.1	$\mu\text{A}$	
Emitter Base Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	-	0.1	$\mu\text{A}$	
Collector Base Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	50	-	V	
Collector Emitter Breakdown Voltage at $-I_C = 10\text{ mA}$	$-V_{(BR)CEO}$	50	-	V	
Emitter Base Breakdown Voltage at $-I_E = 10\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	-	V	
Collector Emitter Saturation Voltage at $-I_C = 100\text{ mA}$ , $-I_B = 10\text{ mA}$	$-V_{CE(sat)}$	-	0.3	V	
Base Emitter Saturation Voltage at $-I_C = 100\text{ mA}$ , $-I_B = 10\text{ mA}$	$-V_{BE(sat)}$	-	1.1	V	
Gain Bandwidth Product at $-V_{CE} = 10\text{ V}$ , $-I_C = 1\text{ mA}$	$f_T$	80	-	MHz	
Output Capacitance at $-V_{CB} = 10\text{ V}$ , $f = 1\text{ MHz}$	$C_{OB}$	-	7	pF	

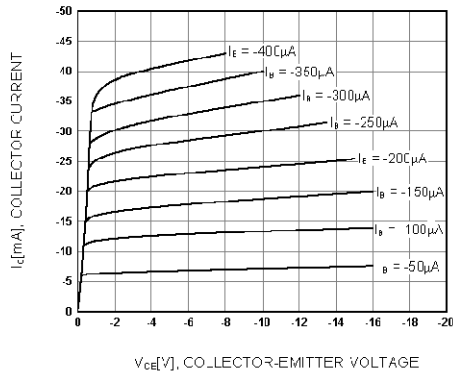


Figure 1. Static Characteristic

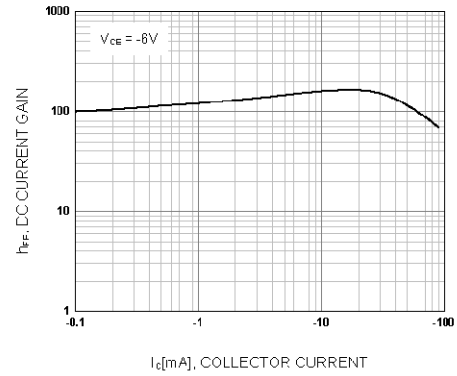


Figure 2. DC current Gain

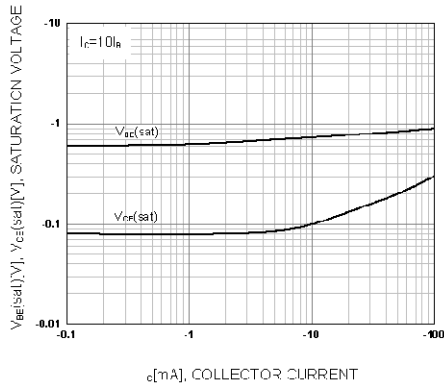


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

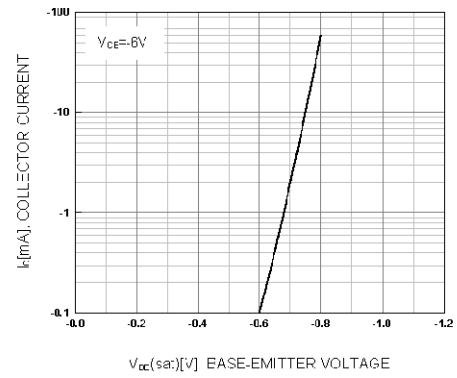


Figure 4. Base-Emitter On Voltage

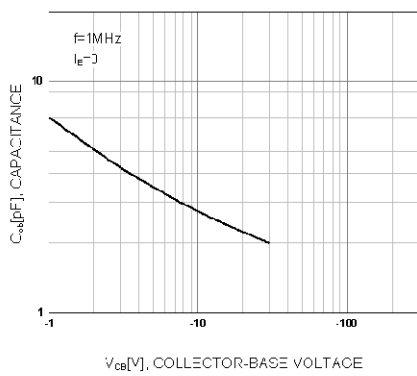


Figure 5. Collector Output Capacitance

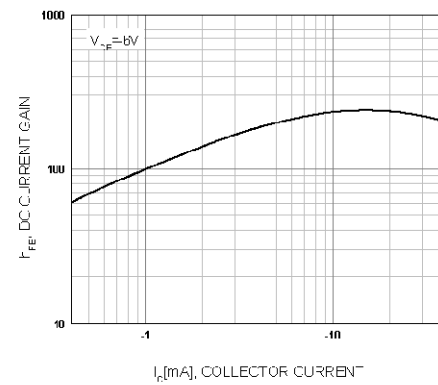


Figure 6. Current Gain Bandwidth Product

## **PACKAGE OUTLINE**

**Plastic surface mounted package; 3 leads**

**SOT-23**

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